

2N3054
2N3054A

**SILICON
NPN POWER TRANSISTORS**



TO-66 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N3054, 2N3054A devices are silicon NPN power transistors manufactured by the epitaxial base process, mounted in a hermetically sealed metal case, designed for general purpose amplifier and switching applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_C=25^{\circ}\text{C}$)

Collector-Base Voltage
Collector-Emitter Voltage
Collector-Emitter Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Continuous Base Current
Power Dissipation (2N3054)
Power Dissipation (2N3054A)
Operating and Storage Junction Temperature
Thermal Resistance (2N3054)
Thermal Resistance (2N3054A)

SYMBOL		UNITS
V_{CBO}	90	V
V_{CEV}	90	V
V_{CER}	60	V
V_{CEO}	55	V
V_{EBO}	7.0	V
I_C	4.0	A
I_B	2.0	A
P_D	25	W
P_D	75	W
T_J, T_{stg}	-65 to +200	$^{\circ}\text{C}$
Θ_{JC}	7.0	$^{\circ}\text{C/W}$
Θ_{JC}	2.33	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CEV}	$V_{CE}=90\text{V}, V_{EB}=1.5\text{V}$		1.0	mA
I_{CEV}	$V_{CE}=90\text{V}, V_{EB}=1.5\text{V}, T_C=150^{\circ}\text{C}$		6.0	mA
I_{CEO}	$V_{CE}=30\text{V}$		500	μA
I_{EBO}	$V_{EB}=7.0\text{V}$		1.0	mA
BV_{CEO}	$I_C=100\text{mA}$	55		V
BV_{CER}	$I_C=100\text{mA}, R_{BE}=100\Omega$	60		V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		1.0	V
$V_{CE(SAT)}$	$I_C=3.0\text{A}, I_B=1.0\text{A}$		6.0	V
$V_{BE(ON)}$	$V_{CE}=4.0\text{V}, I_C=500\text{mA}$		1.7	V
h_{FE}	$V_{CE}=4.0\text{V}, I_C=500\text{mA}$	25	150	
h_{FE}	$V_{CE}=4.0\text{V}, I_C=3.0\text{A}$	5.0		
h_{fe}	$V_{CE}=4.0\text{V}, I_C=100\text{mA}, f=1.0\text{kHz}$	25	180	
f_T	$V_{CE}=10\text{V}, I_C=200\text{mA}, f=1.0\text{MHz}$	3.0		MHz
f_{hfe}	$V_{CE}=4.0\text{V}, I_C=100\text{mA}$	30		kHz

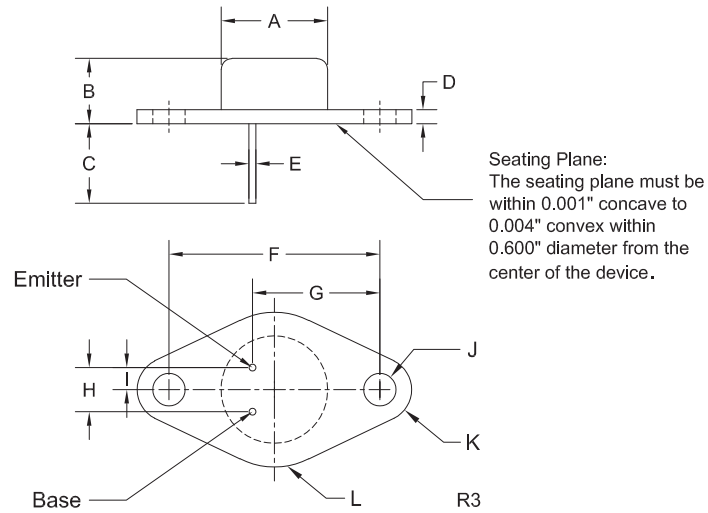
R2 (2-September 2014)

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TO-66 CASE - MECHANICAL OUTLINE



MARKING:
FULL PART NUMBER

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.470	0.500	11.94	12.70
B	0.250	0.340	6.35	8.64
C	0.360	-	9.14	-
D	0.050	0.075	1.27	1.91
E (DIA)	0.028	0.034	0.71	0.86
F	0.956	0.964	24.28	24.48
G	0.570	0.590	14.48	14.99
H	0.190	0.210	4.83	5.33
I	0.093	0.107	2.36	2.72
J (DIA)	0.142	0.152	3.61	3.86
K (RAD)	0.141		3.58	
L (RAD)	0.345		8.76	

TO-66 (REV:R3)

R2 (2-September 2014)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

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